

Silicon PNP Power Transistors

2SA1103

DESCRIPTION

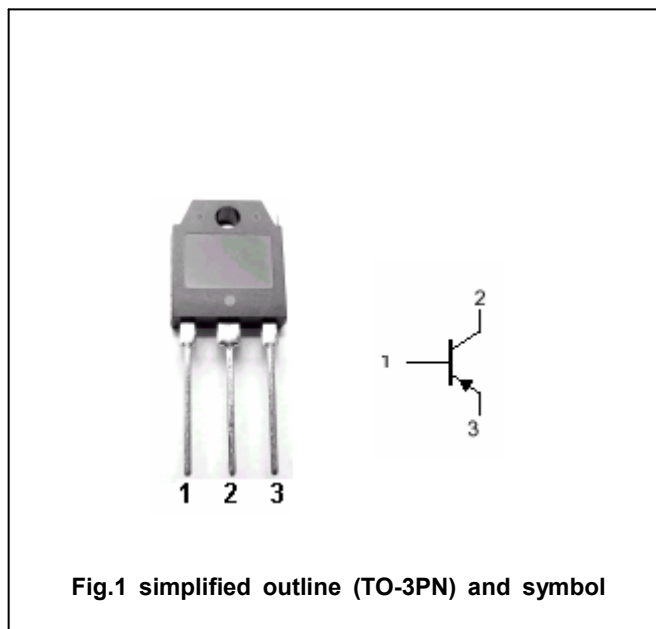
- With TO-3PN package
- Complement to type 2SC2578
- High current capability
- High power dissipation

APPLICATIONS

- Audio power amplifier applications
- DC-DC converters

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-7	A
P_C	Collector power dissipation	$T_C=25$	70	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -25mA$; $I_B = 0$	-100			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -3A$; $I_B = -0.3A$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = -3A$; $I_B = -0.3A$			-1.8	V
I_{CBO}	Collector cut-off current	$V_{CB} = -100V$; $I_E = 0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB} = -6V$; $I_C = 0$			-100	μA
h_{FE}	DC current gain	$I_C = -3A$; $V_{CE} = 4V$	50		180	
f_T	Transition frequency	$I_E = 1A$; $V_{CE} = -12V$		20		MHz

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PACKAGE OUTLINE

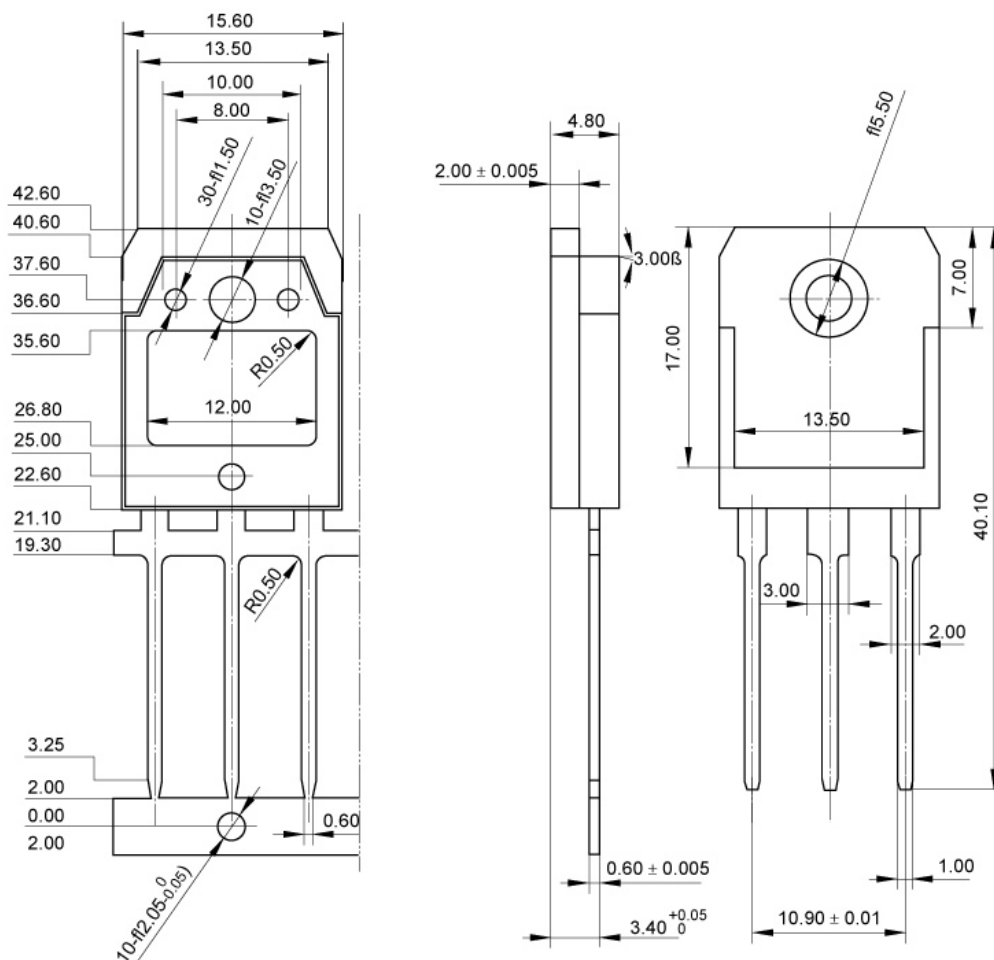


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)